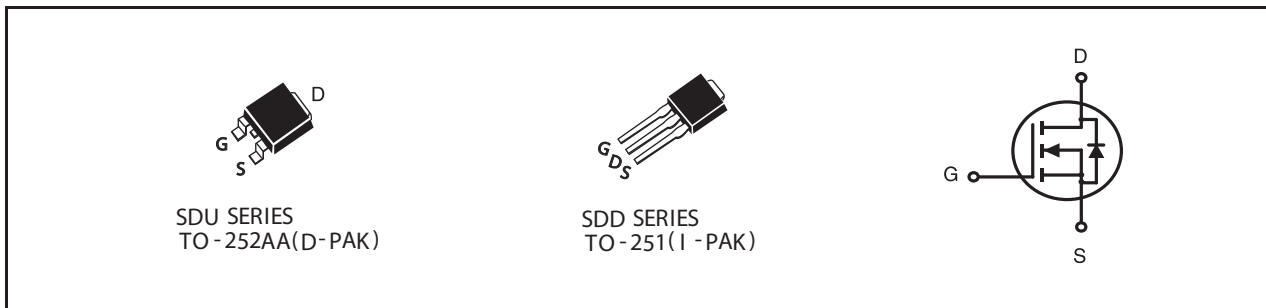


**N-Channel Logic Level Enhancement Mode Field Effect Transistor****PRODUCT SUMMARY**

V _{DSS}	I _D	R _{DS(ON)} (Ω) Max
650V	1A	16 @ V _{GS} =10V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.

**ABSOLUTE MAXIMUM RATINGS** (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	650	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ^a	T _C =25°C	1
		T _C =70°C	0.8
I _{DM}	-Pulsed ^b	2.9	A
E _{AS}	Single Pulse Avalanche Energy ^d	2.5	mJ
P _D	Maximum Power Dissipation	T _C =25°C	42
		T _C =70°C	27
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJC}	Thermal Resistance, Junction-to-Case ^a	3	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient ^a	50	°C/W

SDU/D01N65

Ver 1.0

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250μA	650			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =520V , V _{GS} =0V			1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =0.5A		13	16	ohm
g _{FS}	Forward Transconductance	V _{DS} =20V , I _D =0.5A		0.5		S
DYNAMIC CHARACTERISTICS °						
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V f=1.0MHz		132		pF
C _{OSS}	Output Capacitance			21		pF
C _{RSS}	Reverse Transfer Capacitance			5.8		pF
SWITCHING CHARACTERISTICS °						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =325V I _D =0.5A V _{GS} =10V R _{GEN} =6ohm		11.5		ns
t _r	Rise Time			14.5		ns
t _{D(OFF)}	Turn-Off Delay Time			16.5		ns
t _f	Fall Time			14		ns
Q _g	Total Gate Charge		V _{DS} =325V, I _D =0.5A, V _{GS} =10V		3	
Q _{gs}	Gate-Source Charge	V _{DS} =325V, I _D =0.5A, V _{GS} =10V		1		nC
Q _{gd}	Gate-Drain Charge			1.1		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =0.3A		0.79	1.4	V
Notes a.Surface Mounted on FR4 Board, t < 10sec. b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%. c.Guaranteed by design, not subject to production testing. d.Starting T _J =25°C, L=5mH, V _{DD} = 100V.(See Figure13)						

Aug,19,2010

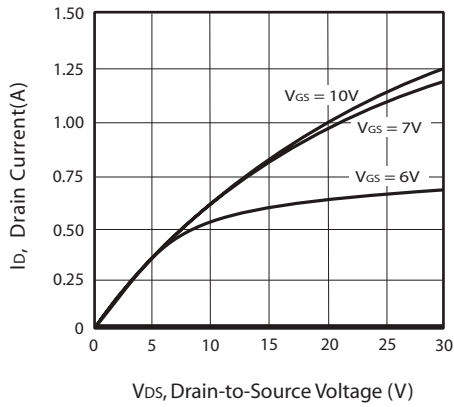


Figure 1. Output Characteristics

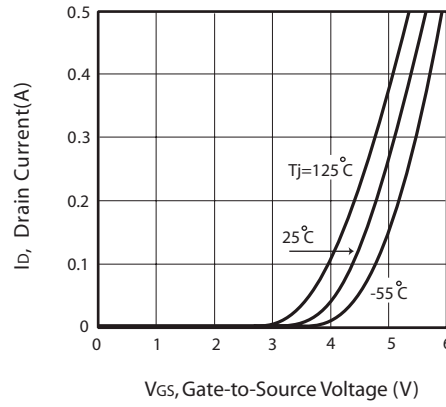


Figure 2. Transfer Characteristics

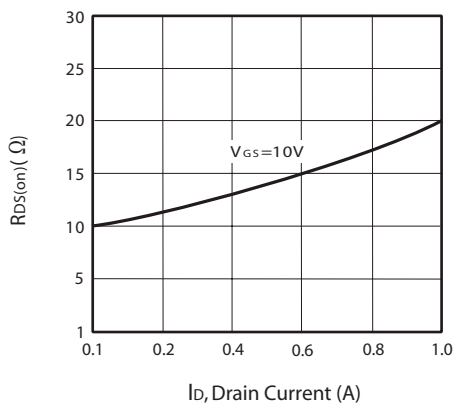


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

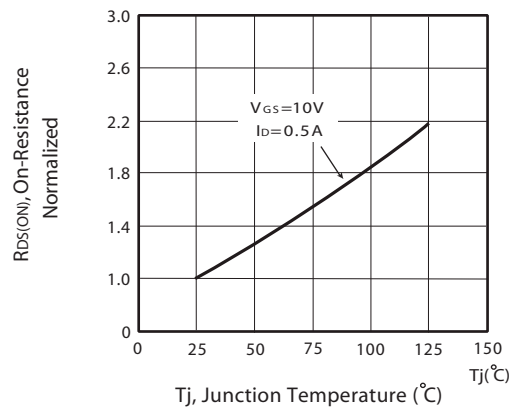


Figure 4. On-Resistance Variation with Drain Current and Temperature

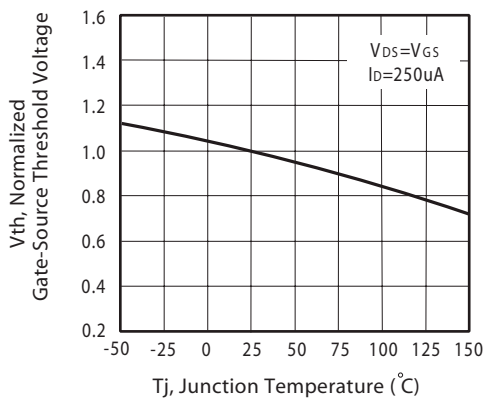


Figure 5. Gate Threshold Variation with Temperature

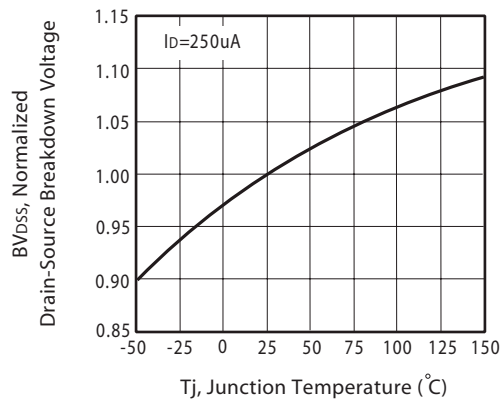


Figure 6. Breakdown Voltage Variation with Temperature

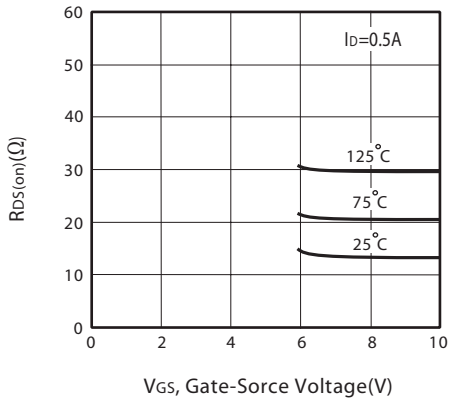


Figure 7. On-Resistance vs. Gate-Source Voltage

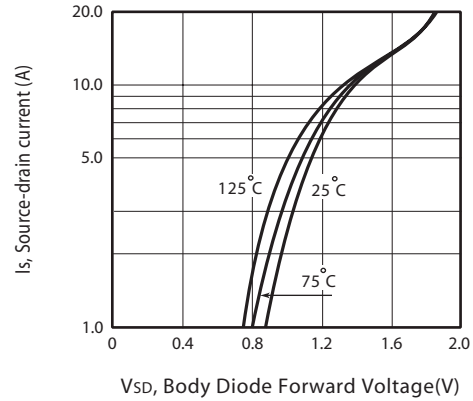


Figure 8. Body Diode Forward Voltage Variation with Source Current

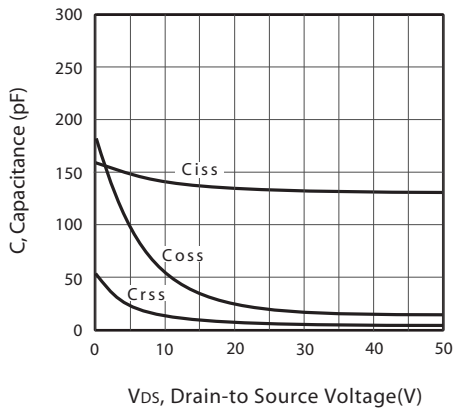


Figure 9. Capacitance

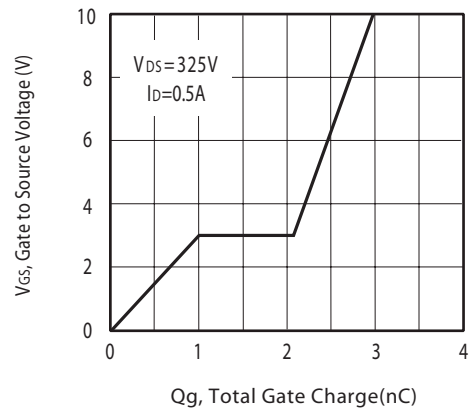


Figure 10. Gate Charge

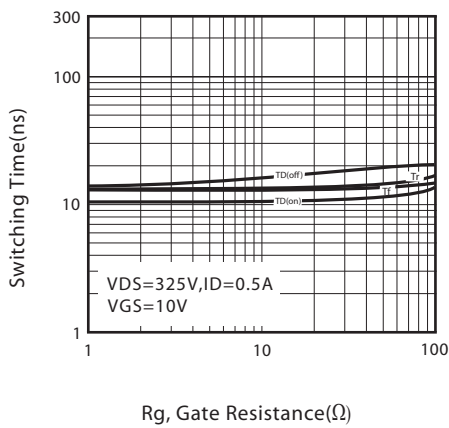


Figure 11. switching characteristics

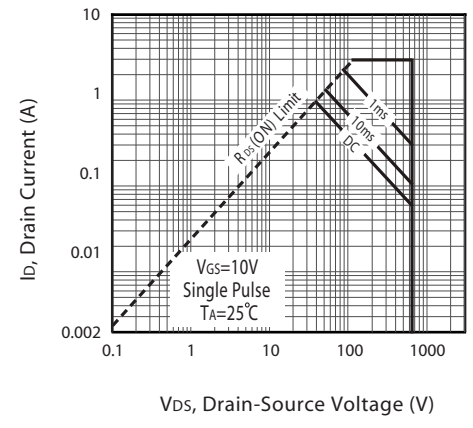
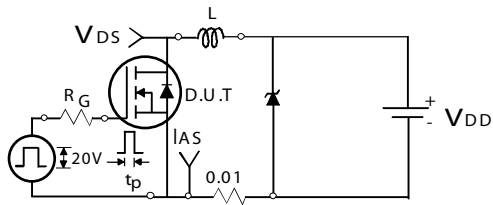
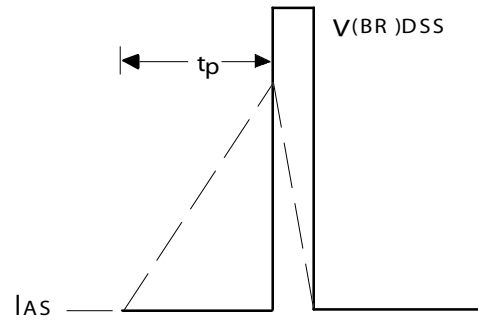


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

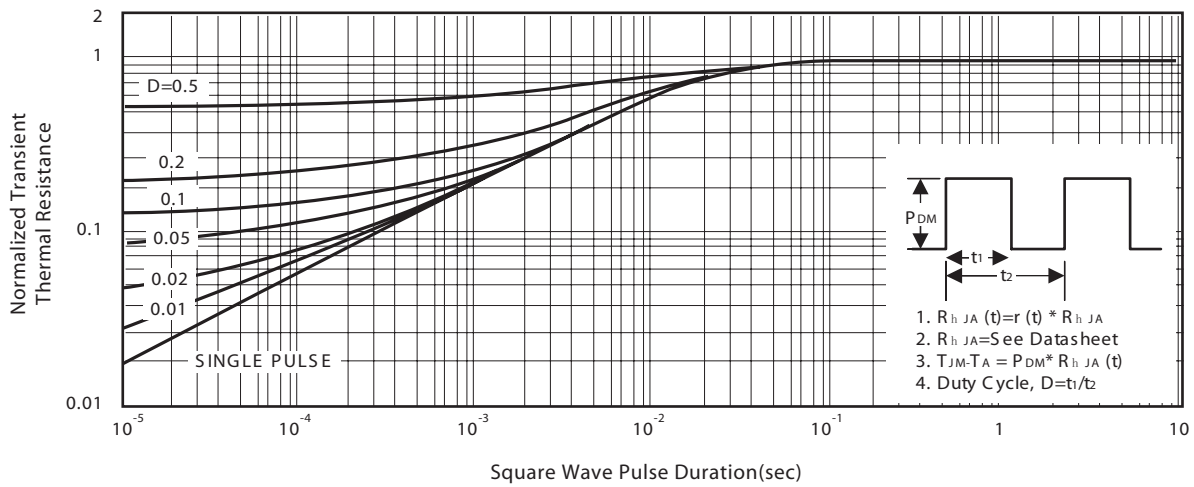
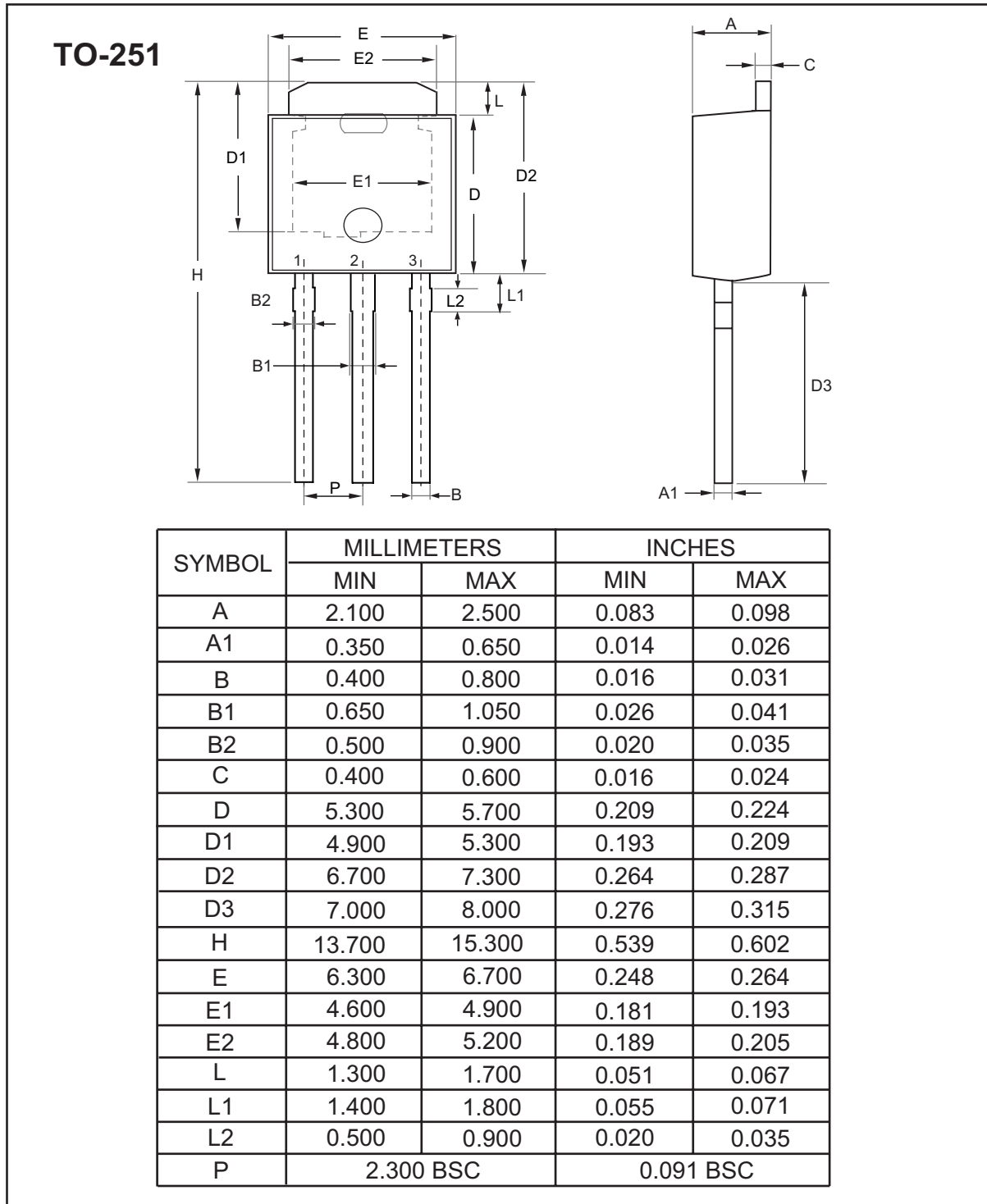


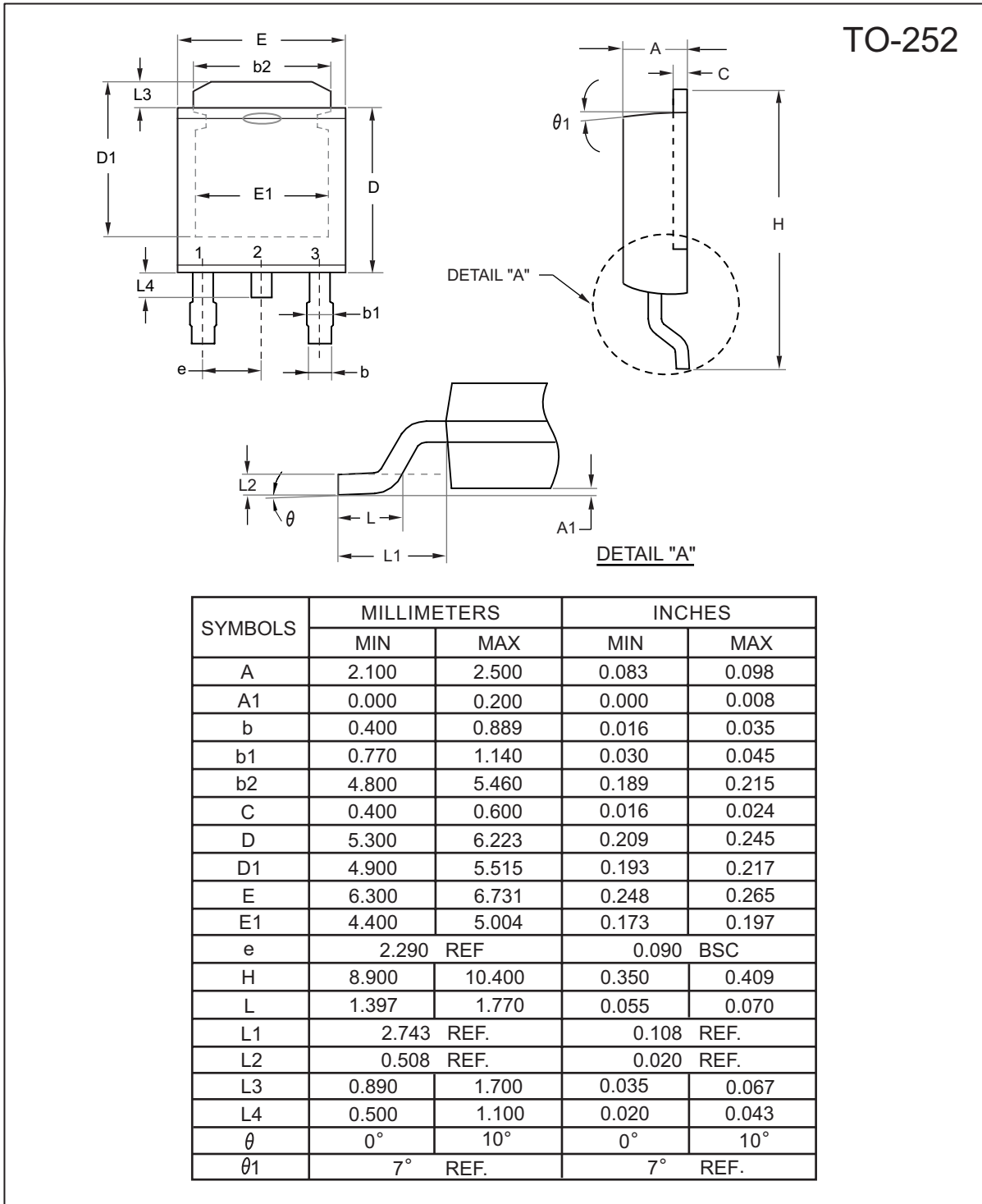
Figure 14. Normalized Thermal Transient Impedance Curve

PACKAGE OUTLINE DIMENSIONS



SDU/D01N65

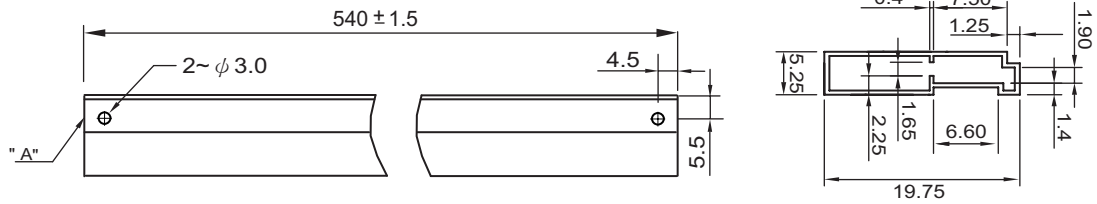
Ver 1.0



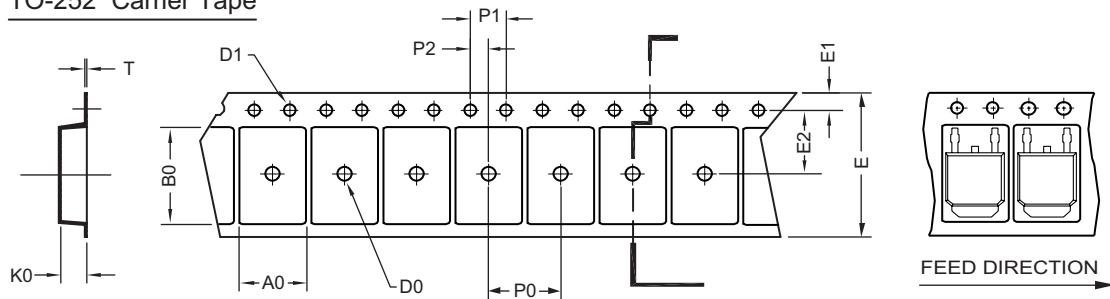
Aug,19,2010

TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



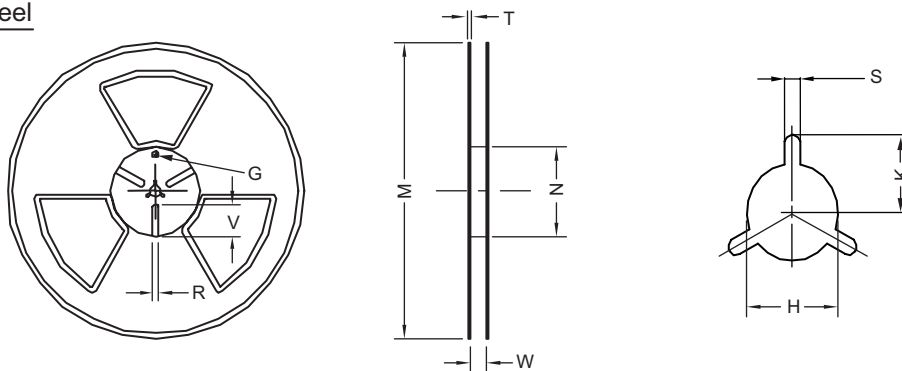
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ 2	φ 1.5 + 0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---